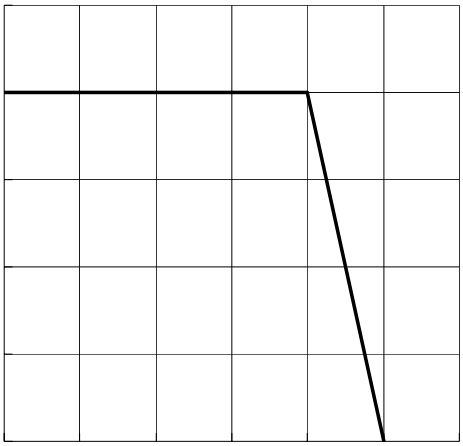
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	200	V
RMS Voltage	V_{RMS}	140	V
DC Blocking Voltage	V_{DC}	200	V
Average Rectified Forward Current	I_F	2×6	A
Non Repetitive Peak Surge Current	I_{FSM}	100	A
Thermal Resistance Junction to Case	R_{Jc}	2.9	/W
Storage Temperature Range	T_j T_{stg}	-55 150	

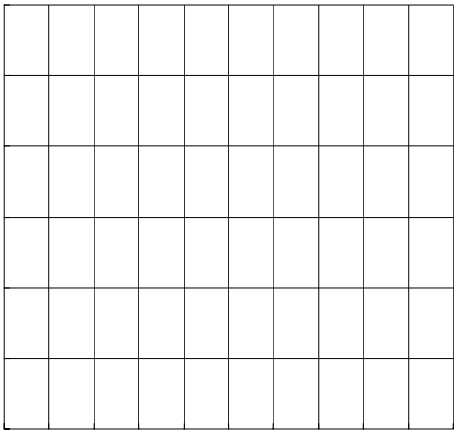
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	I_F =2.0A(T_C=25)		0.82		V
		I_F =2.0A(T_C=125)		0.68		V
		I_F =6.0A(T_C=25)		0.92	1.0	V
		I_F =6.0A(T_C=125)		0.82	0.9	V
Instantaneous Reverse Current	I_R	V_R=200V(T_a=25)			10	A
		V_R=200V(T_a=125)			150	A
Reverse Recovery Time	t_{rr}	I_F=0.5A I_R=1.0A I_{RR}=0.25A			35	ns

Notes

/Short duration pulse test used to minimize self-heating effect.

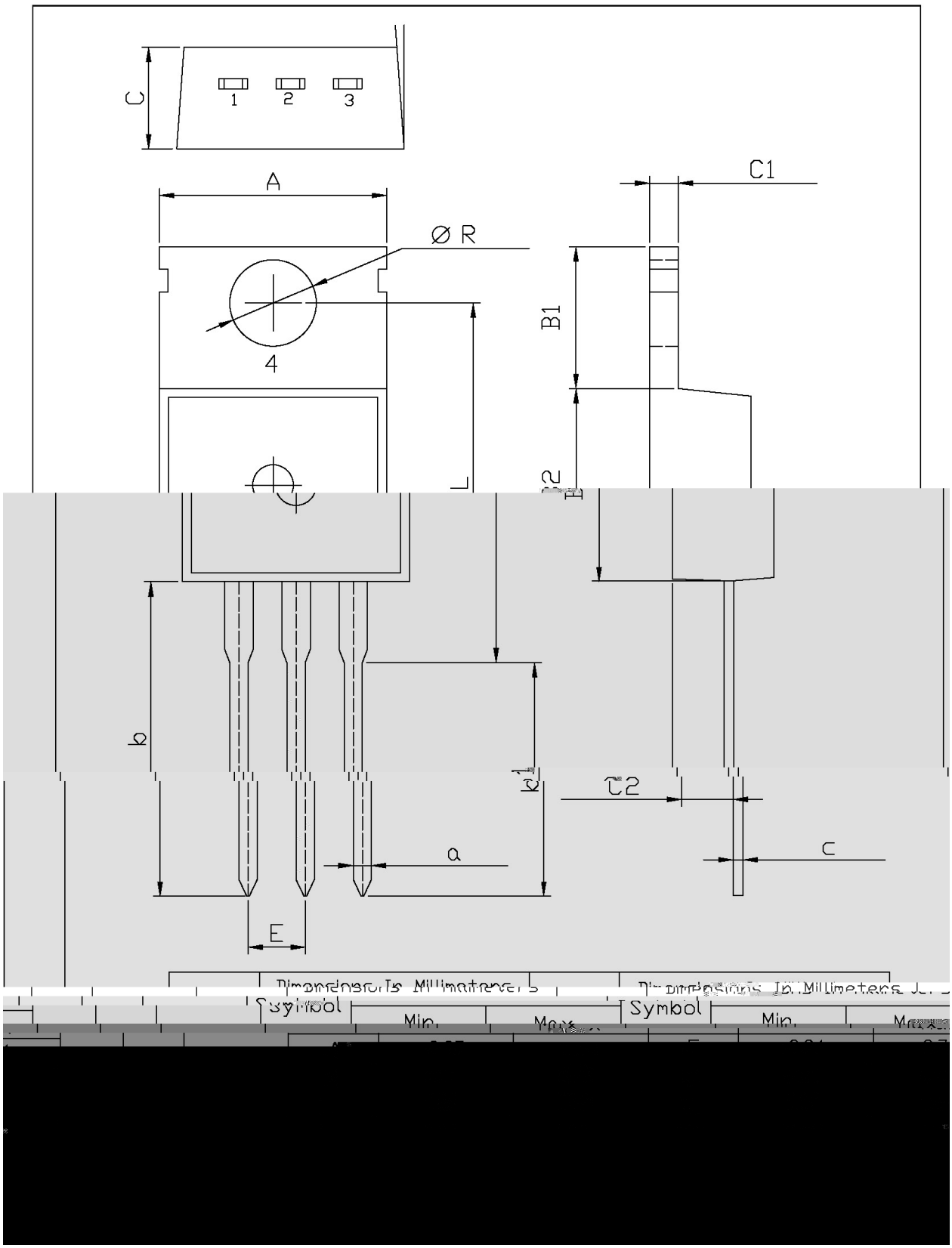
/ Unless otherwise noted, values for the parameters of a single chip



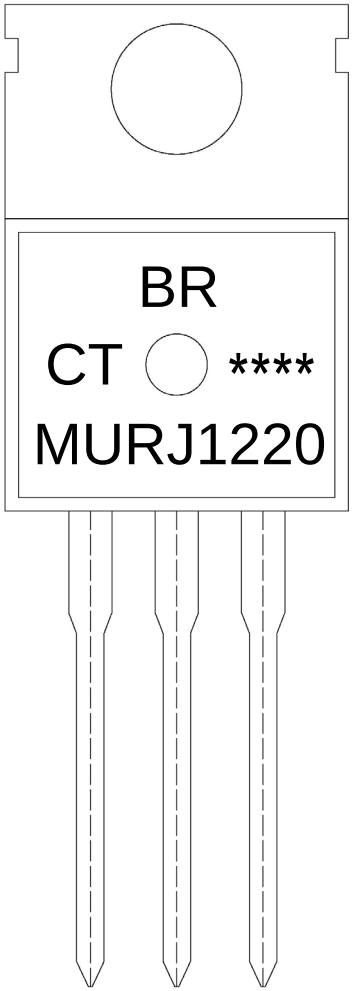


TO-220S

Unit: mm



Dimensions In Millimeters			Dimensions In Millimeters		
Symbol	Min.	Max.	Symbol	Min.	Max.



Note:

BR:	Company Code
MURJ1220	Product Type.
CT:	Internal Structure
****:	Lot No. Code, code change with Lot No.

1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 255 5 5 0.5sec;	2.Peak Temp.:255 5 , Duration:5 0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

270 5 10 1 sec. Temp.:270±5 Time:10±1 sec

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-220S	50	20	1000	5	5000	532×31.4×5.5	555×164×50	575×290×180